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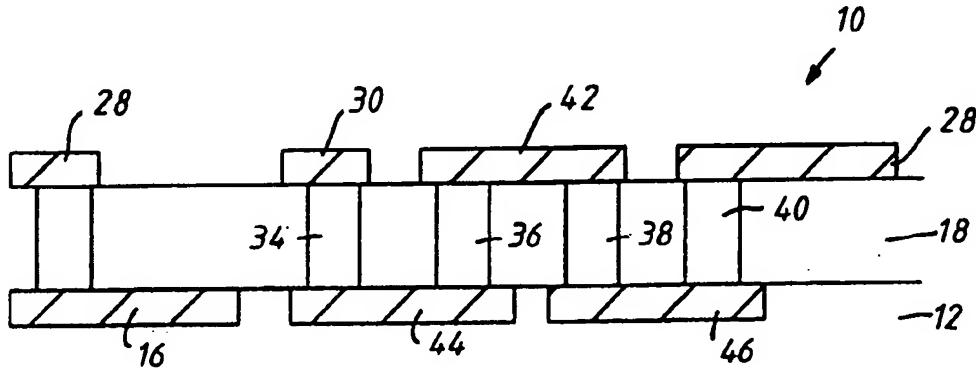
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(54) Title: ELECTRONIC STRUCTURE HAVING IN-SITU RESISTORS

WO 02/31867 A2



(57) Abstract: Electronic structure that has in-situ formed resistors consists of a first plurality of conductive elements formed in an insulating material layer, a plurality of electrically resistive vias formed on top and in electrical communication with at least one of the first plurality of conductive elements, and a second plurality of conductive elements formed on top of and in electrical communication with at least one of the plurality of electrically resistive vias. The structure may further be formed in a multi-level configuration such that multi-level resistors may be connected in-series to provide larger resistance values. The structure may be combined with a capacitor network to form RC circuits.